

N-Channel 100V(D-S) MOSFET

Product summary		
V_{DS}	100	V
$R_{DS(ON)}$ (at $V_{GS}=10V$) Typ.	18	$m\Omega$
$I_D(T_c=25^\circ C)$	40	A

Features

- Advanced Trench Technology
- Low Gate Charge

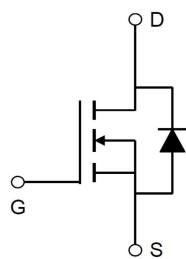
Applications

- PWM Application
- Load switching

Pin Configuration



TO-252



Packing Information

Device	Package	Reel Size	Quantity(Min. Package)
ECFA40N10	TO-252	13"	2500pcs

Absolute Maximum Ratings (at $T_A=25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_c=25^\circ C$	A
		$T_c=100^\circ C$	A
I_{DM}	Pulse Drain Current Tested ^A	160	A
E_{AS}	Single Pulse Avalanche Energy ^B	144	mJ
P_D	Power Dissipation $T_c=25^\circ C$	105	W
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Typical	Units
R_{eJC}	Thermal Resistance-Junction to case	1.19	°C/W

Electrical Characteristics (at $T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=100\text{V}, V_{\text{GS}}=0\text{V}$	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 20\text{V}$	--	--	± 100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2.0	2.9	4.0	V
$R_{\text{DS}(\text{ON})}$	Drain-Source On-State Resistance ^C	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=20\text{A}$	--	18	24	$\text{m}\Omega$
V_{SD}	Forward Voltage	$I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V}$	--	--	1.2	V
I_{S}	Maximum Body-Diode Continuous Current		--	--	40	A
Dynamic Parameters ^D						
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=25\text{V}$ $f=1\text{MHz}$	--	3810	--	pF
C_{oss}	Output Capacitance		--	195	--	pF
C_{rss}	Reverse Transfer Capacitance		--	153	--	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=50\text{V}, I_{\text{D}}=20\text{A}$ $V_{\text{GS}}=0 \text{ to } 10\text{V}$	--	78	--	nC
Q_{gs}	Gate-Source Charge		--	20	--	nC
Q_{gd}	Gate-Drain Charge		--	22	--	nC
$t_{\text{D}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=50\text{V}, I_{\text{D}}=20\text{A},$ $R_{\text{GEN}}=6\Omega,$ $V_{\text{GS}}=10\text{V}$	--	17	--	ns
t_r	Turn-on Rise Time		--	27	--	ns
$t_{\text{D}(\text{off})}$	Turn-off Delay Time		--	45	--	ns
t_f	Turn-off Fall Time		--	10	--	ns

A. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

B. EAS condition: $T_J=25^\circ\text{C}$, $V_{\text{DD}}=30\text{V}$, $V_G=10\text{V}$, $R_G=25\text{ohm}$, $L=0.5\text{mH}$, $I_{\text{AS}}=24\text{A}$.

C. Pulse Test: Pulse Width $\leq 300\text{us}$, Duty cycle $\leq 0.5\%$.

D. Guaranteed by design, not subject to production testing.

Typical Characteristics

Figure 1: Output Characteristics

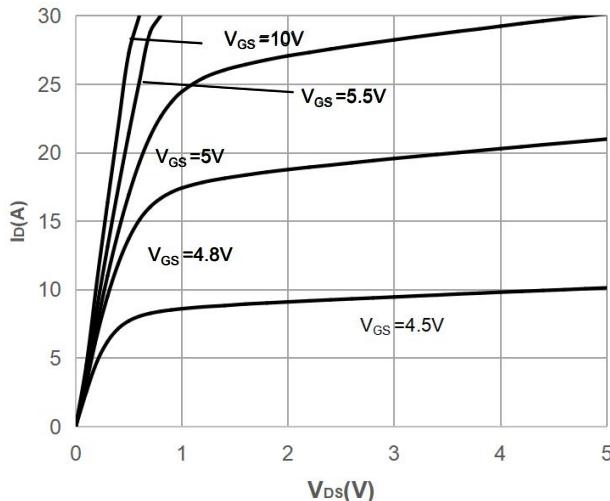


Figure 2: Typical Transfer Characteristics

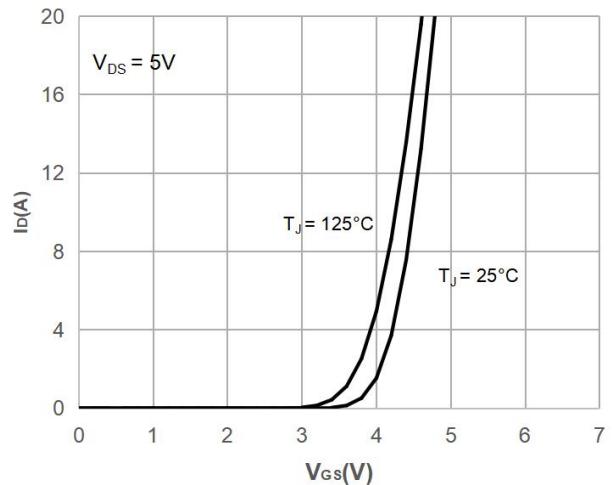


Figure 3: On-resistance vs. Drain Current

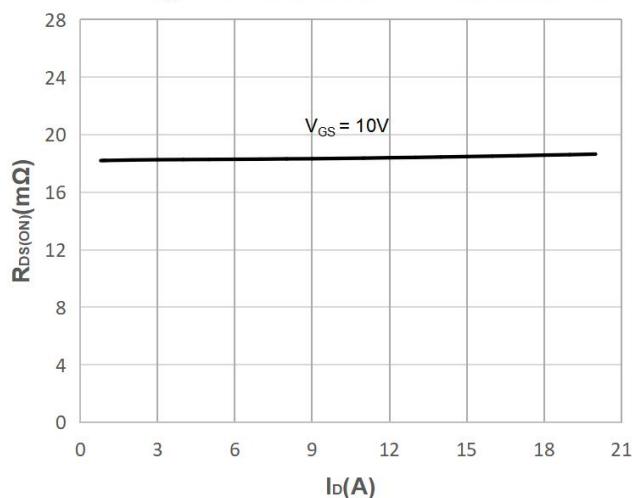


Figure 4: Body Diode Characteristics

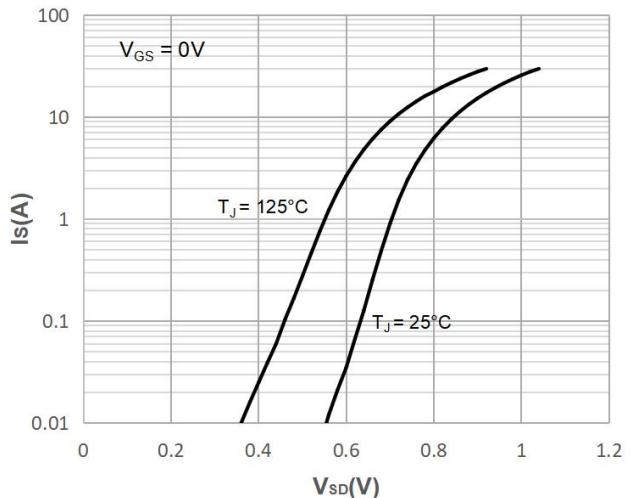


Figure 5: Gate Charge Characteristics

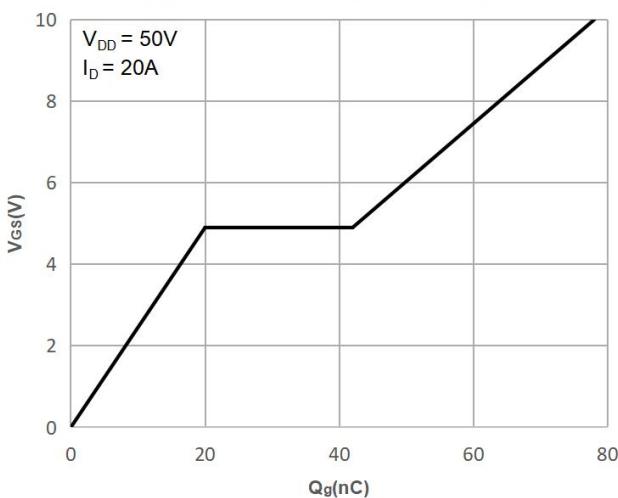
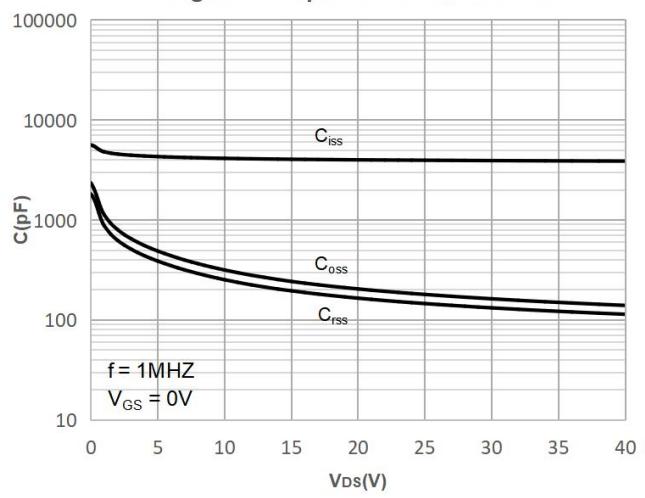


Figure 6: Capacitance Characteristics



Typical Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

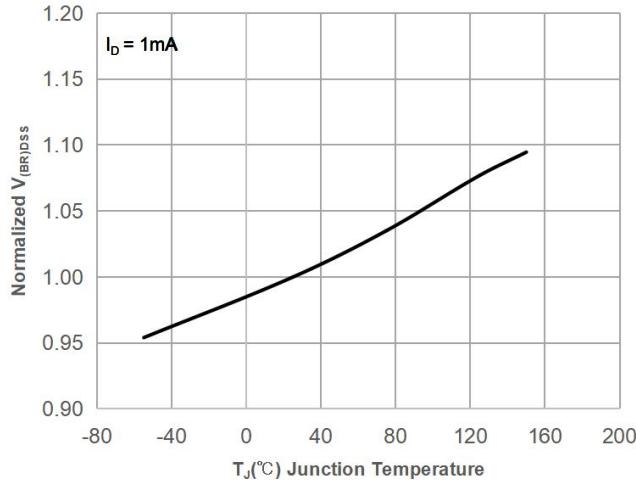


Figure 8: Normalized on Resistance vs. Junction Temperature

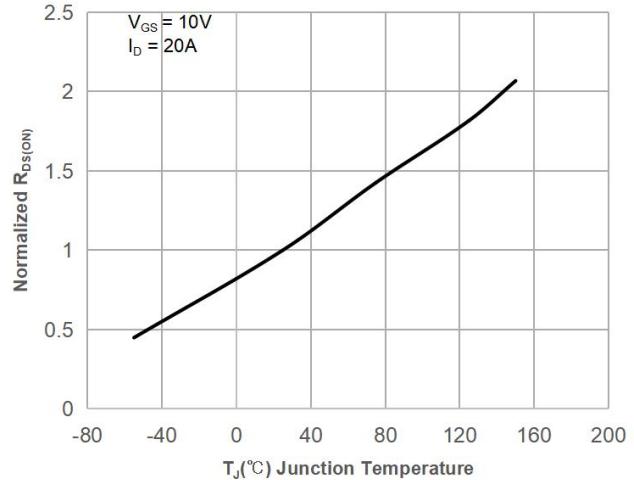


Figure 9: Maximum Safe Operating Area

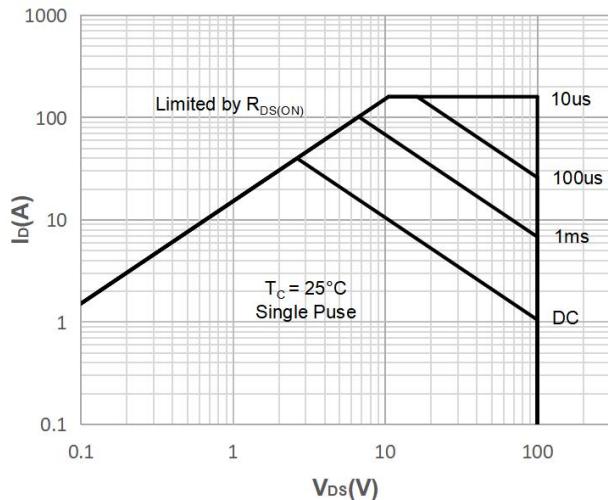


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

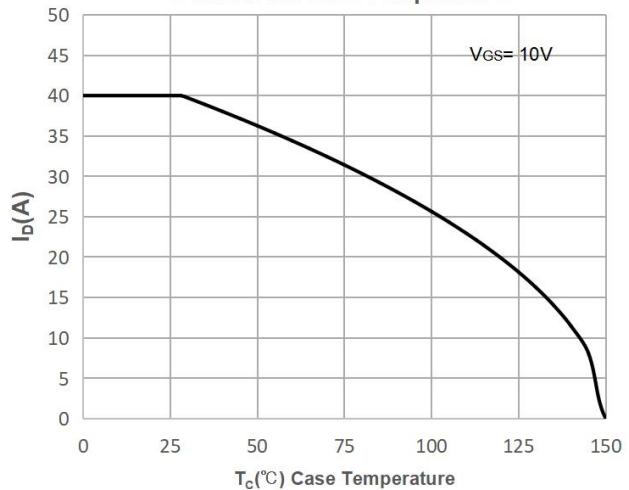


Figure 11: Normalized Maximum Transient Thermal Impedance

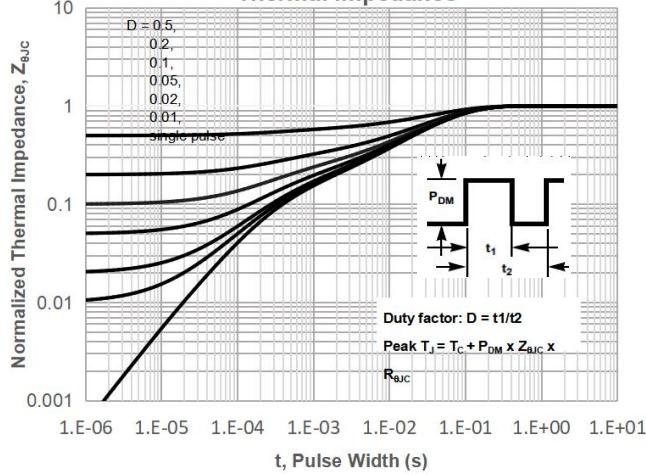
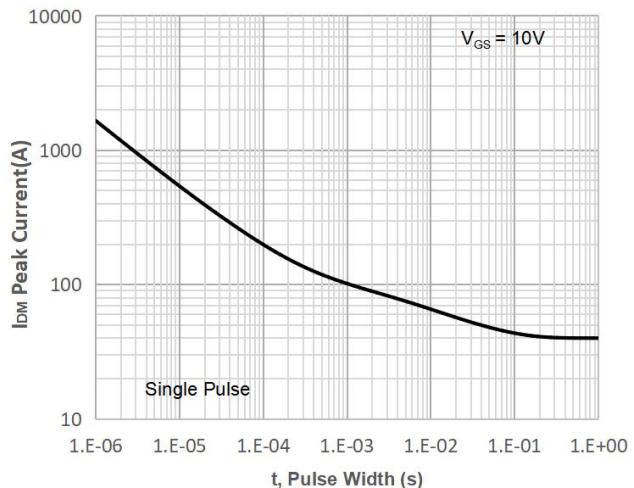


Figure 12: Peak Current Capacity



Test Circuit

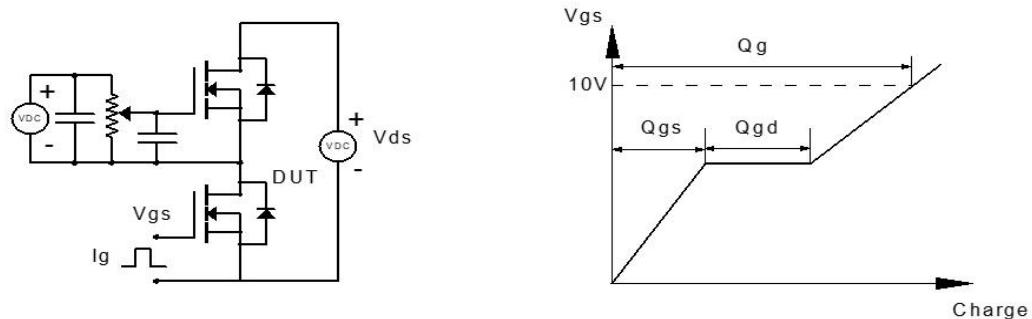


Figure 1: Gate Charge Test Circuit & Waveform

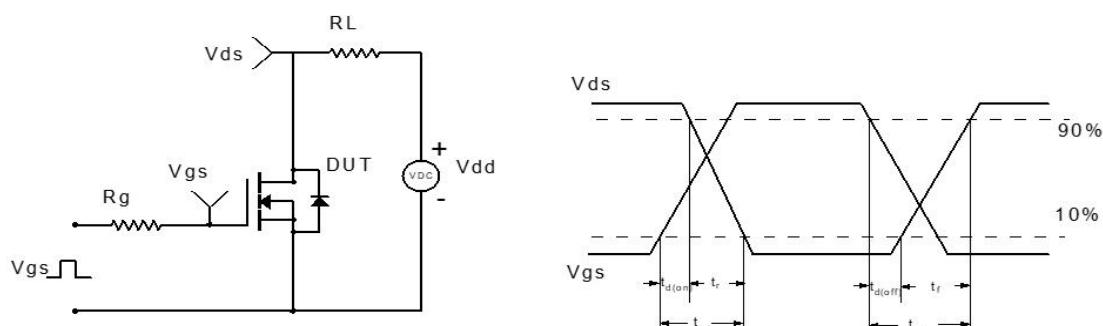


Figure 2: Resistive Switching Test Circuit & Waveform

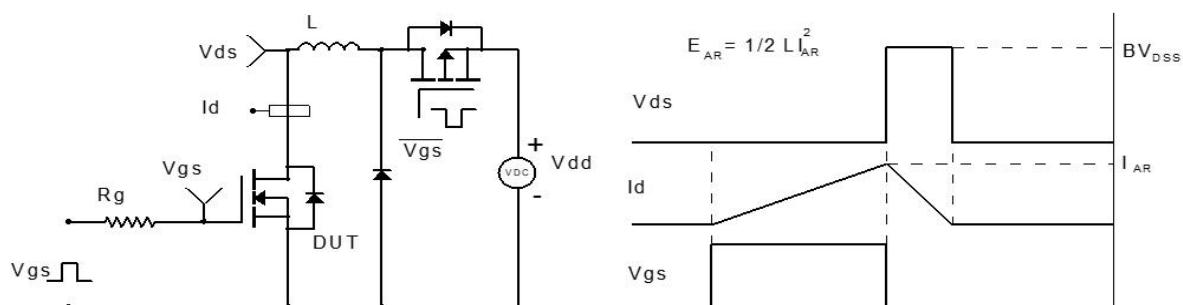


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

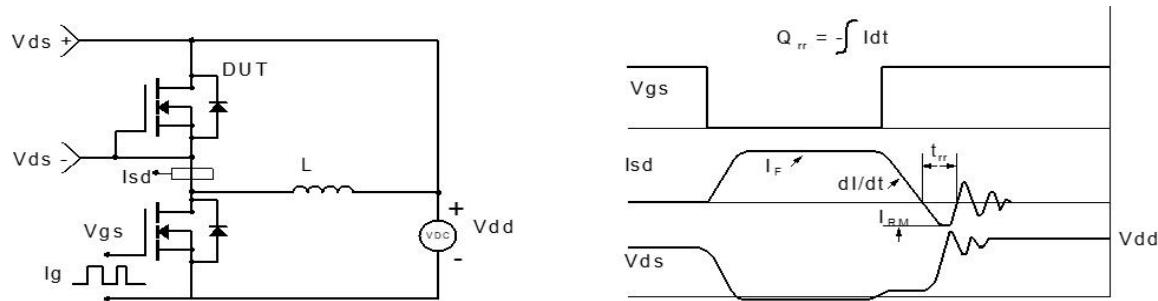
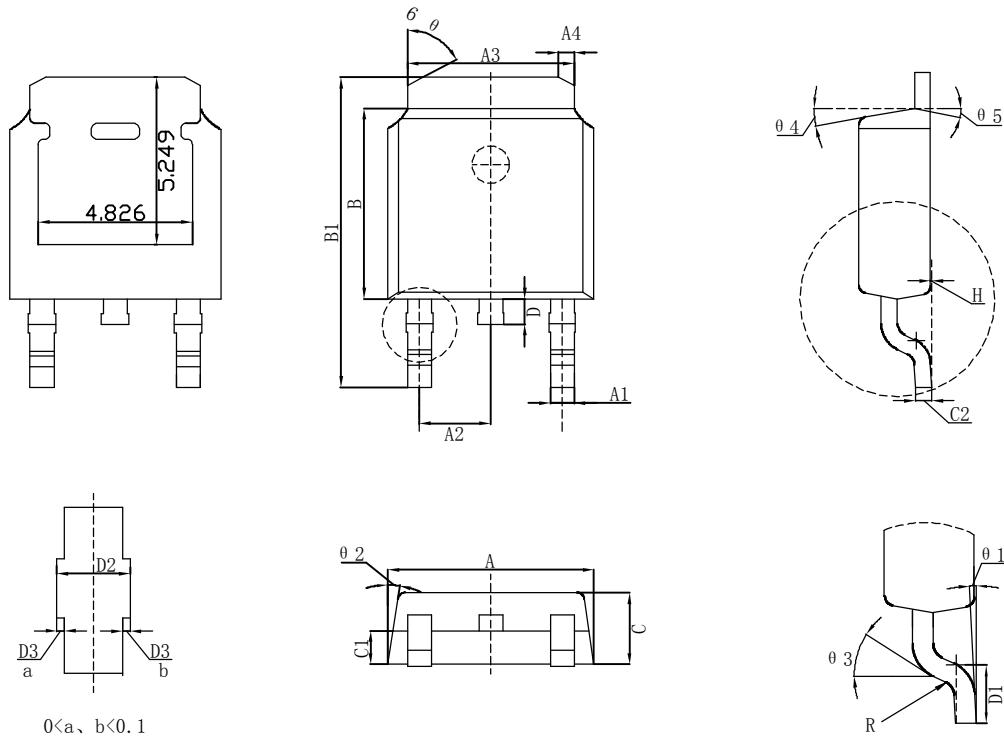


Figure 4: Diode Recovery Test Circuit & Waveform

TO-252 Package Information



标注	尺寸	最小(mm)	最大(mm)	标注	尺寸	最小(mm)	最大(mm)
A		6.50	6.70	D1		1.40	1.60
A1		0.71	0.81	D2		0.81	0.91
A2		2.236	2.336	D3		0.05TYP	
A3		5.284	5.384	H		0.00	0.10
A4		0.75	0.85	R		0.40TYP	
B		6.00	6.20	θ1		0° - 8°	
B1		9.80	10.10	θ2		8.5° TYP4	
C		2.20	2.40	θ3		25° TYP	
C1		0.967	1.087	θ4		10° TYP2	
C2		0.498	0.518	θ5		10° TYP	
D		0.70	0.90	θ6		70° TYP	